

HD74ALVC1G125

Bus Buffer Gate with 3-state Output

REJ03D0129-0300Z (Previous ADE-205-617B (Z)) Rev.3.00 Nov.12.2003

Description

The HD74ALVC1G125 has a bus buffer gate with 3-state output in a 5 pin package. Output is disabled when the associated output enable (\overline{OE}) input is high. To ensure the high impedance state during power up or power down, \overline{OE} should be connected to V_{CC} through a pull-up resistor; the minimum value of the resistor is determined by the current sinking capability of the driver. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Supply voltage range: 1.2 to 3.6 V Operating temperature range: -40 to +85°C
- All inputs V_{IH} (Max.) = 3.6 V (@ V_{CC} = 0 V to 3.6 V)

All outputs
$$V_0$$
 (Max.) = 3.6 V (@ V_{CC} = 0 V)

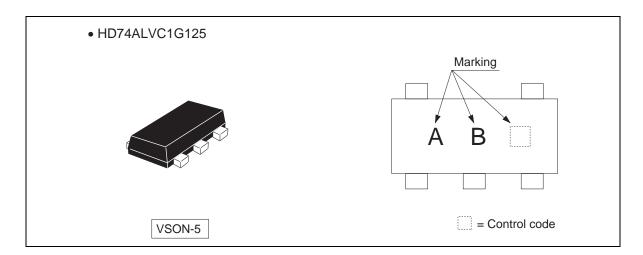
• Output current ± 2 mA (@V_{CC} = 1.2 V) ± 4 mA (@V_{CC} = 1.4 V to 1.6 V) ± 6 mA (@V_{CC} = 1.65 V to 1.95 V) ± 18 mA (@V_{CC} = 2.3 V to 2.7 V)

 $\pm 24 \text{ mA} (@V_{CC} = 3.0 \text{ V to } 3.6 \text{ V})$

Ordering Information

			Package	Taping Abbreviation
Part Name	Package Type	Package Code	Abbreviation	(Quantity)
HD74ALVC1G125VSE	VSON-5 pin	TNP-5DV	VS	E (3,000 pcs/reel)

Outline and Article Indication



Function Table

Inputs

ŌĒ	A	Output Y
L	Н	Н
L	L	L
Н	X	Z

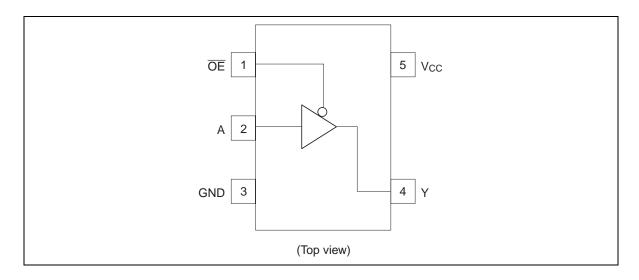
H: High level

L: Low level

X: Immaterial

Z: High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V _{CC}	-0.5 to 4.6	V	
Input voltage range *1	VI	-0.5 to 4.6	V	
Output voltage range *1, 2	Vo	-0.5 to V _{CC} +0.5	V	Output: H or L or Z
		-0.5 to 4.6		V _{CC} : OFF
Input clamp current	I _{IK}	-50	mA	V _I < 0
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	l ₀	±50	mA	$V_O = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I _{CC} or I _{GND}	±100	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

HD74ALVC1G125

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{CC}	1.2	3.6	V	
Input voltage range	VI	0	3.6	V	
Output voltage range	Vo	0	Vcc	V	
Output current	I _{OH}	_	-2	mA	V _{CC} = 1.2 V
		_	-4		V _{CC} = 1.4 V
		_	-6		V _{CC} = 1.65 V
		_	-18		V _{CC} = 2.3 V
		_	-24		V _{CC} = 3.0 V
	I _{OL}	_	2		V _{CC} = 1.2 V
		_	4		V _{CC} = 1.4 V
			6		V _{CC} = 1.65 V
			18		V _{CC} = 2.3 V
		_	24		V _{CC} = 3.0 V
Input transition rise or fall rate	Δt / Δν	0	20	ns / V	V _{CC} = 1.2 to 2.7 V
		0	10		V _{CC} = 3.3±0.3 V
Operating free-air temperature	Та	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	$V_{CC}(V)^*$	Min	Тур	Max	Unit	Test conditions
Input voltage	V _{IH}	1.2	V _{CC} ×0.75	_	_	V	
		1.4 to 1.6	V _{CC} ×0.7	_	_	_	
		1.65 to 1.95	V _{CC} ×0.7	_	_	_	
		2.3 to 2.7	1.7	_	_	_	
		3.0 to 3.6	2.0	_	_	_	
	V _{IL}	1.2	_	_	V _{CC} ×0.25	_	
		1.4 to 1.6	_	_	V _{CC} ×0.3	_	
		1.65 to 1.95	_	_	V _{CC} ×0.3	_	
		2.3 to 2.7	_	_	0.7	_	
		3.0 to 3.6	_	_	0.8	=	
Output voltage	V _{OH}	Min to Max	V _{CC} -0.2	_	_	V	$I_{OH} = -100 \mu A$
		1.2	0.9	_	_	=	$I_{OH} = -2 \text{ mA}$
		1.4	1.1	_	_	=	$I_{OH} = -4 \text{ mA}$
		1.65	1.2	_	_	=	$I_{OH} = -6 \text{ mA}$
		2.3	1.7	_	_	=	$I_{OH} = -18 \text{ mA}$
		3.0	2.2	_	_	=	$I_{OH} = -24 \text{ mA}$
	V _{OL}	Min to Max	_	_	0.2	=	$I_{OL} = 100 \mu\text{A}$
		1.2	_	_	0.3	_	I _{OL} = 2 mA
		1.4	_	_	0.3	=	I _{OL} = 4 mA
		1.65	_	_	0.3	=	I _{OL} = 6 mA
		2.3	_	_	0.55	_	I _{OL} = 18 mA
		3.0	_	_	0.55	=	I _{OL} = 24 mA
Input current	I _{IN}	3.6	_	_	±5	μΑ	V _{IN} = 3.6 V or GND
Off state output current	l _{OZ}	3.6	_	_	±5	μΑ	$V_O = V_{CC}$ or GND
Quiescent supply current	I _{CC}	3.6	_	_	10	μΑ	$V_{IN} = V_{CC}$ or GND, $I_O = 0$
Output leakage current	I _{OFF}	0	_	_	5	μΑ	V _{IN} or V _O = 0 to 3.6 V
Input capacitance	C _{IN}	3.3	_	4.0	_	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

 $V_{CC} = 1.2 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	_	5.5	_	ns	C _L = 15 pF	А	Υ
Enable time	t _{ZH} t _{ZL}	_	6.5	_	ns	C _L = 15 pF	ŌĒ	Υ
Disable time	t _{HZ} t _{LZ}	_	4.5	_	ns	C _L = 15 pF	ŌĒ	Υ

 $V_{CC} = 1.5 \pm 0.1 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	2.0	_	7.0	ns	$C_L = 15 pF$	Α	Υ
Enable time	t _{ZH} t _{ZL}	2.0	_	7.0	ns	C _L = 15 pF	ŌĒ	Υ
Disable time	t _{HZ} t _{LZ}	2.0	_	7.0	ns	$C_L = 15 pF$	ŌĒ	Υ

 $V_{CC} = 1.8 \pm 0.15 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.5	_	5.0	ns	$C_L = 30 pF$	Α	Υ
Enable time	t _{ZH} t _{ZL}	1.5	_	5.0	ns	C _L = 30 pF	ŌĒ	Y
Disable time	t _{HZ} t _{LZ}	1.5	—	5.0	ns	C _L = 30 pF	ŌĒ	Y

Switching Characteristics (cont)

 $V_{CC} = 2.5 \pm 0.2 \text{ V}$

Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.0	_	4.0	ns	$C_L = 30 pF$	Α	Y
Enable time	t _{ZH} t _{ZL}	1.0	_	4.0	ns	C _L = 30 pF	ŌĒ	Y
Disable time	t _{HZ} t _{LZ}	1.0	_	4.0	ns	$C_L = 30 pF$	ŌĒ	Y

 $V_{CC} = 3.3 \pm 0.3 \text{ V}$

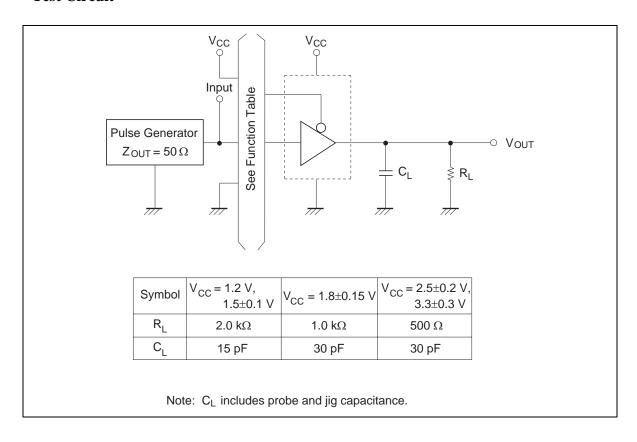
Item	Symbol	Min	Тур	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time	t _{PLH} t _{PHL}	1.0	_	3.0	ns	$C_L = 30 pF$	Α	Υ
Enable time	t _{ZH} t _{ZL}	1.0	_	3.0	ns	C _L = 30 pF	ŌĒ	Υ
Disable time	t _{HZ} t _{LZ}	1.0	_	3.0	ns	$C_L = 30 pF$	ŌĒ	Υ

Operating Characteristics

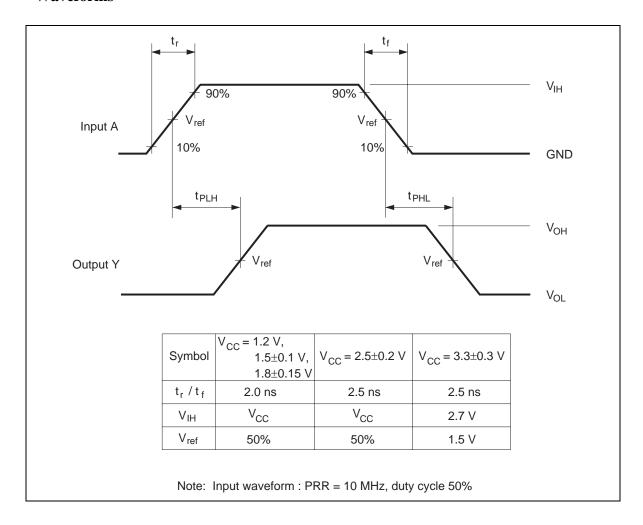
 $(Ta = 25^{\circ}C)$

Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	Test conditions
Power dissipation capacitance	C _{PD}	1.5	_	9.5	_	pF	f = 10 MHz
		1.8	_	9.5	_	_	
		2.5	_	10.0	_		
		3.3		11.0	_	_	

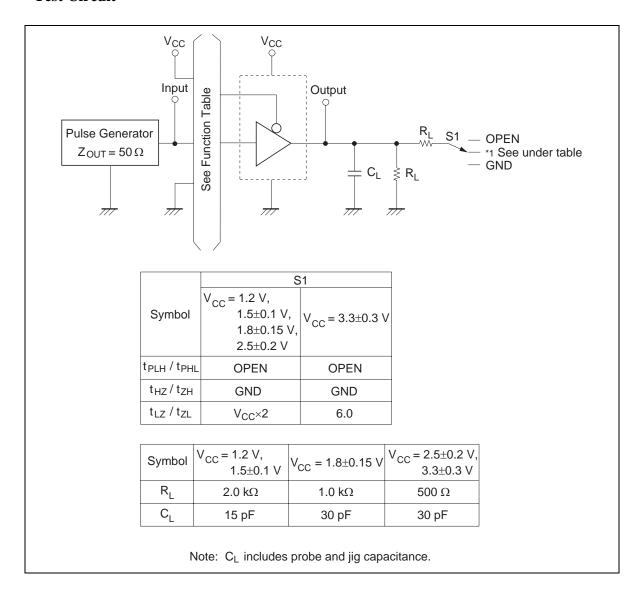
Test Circuit



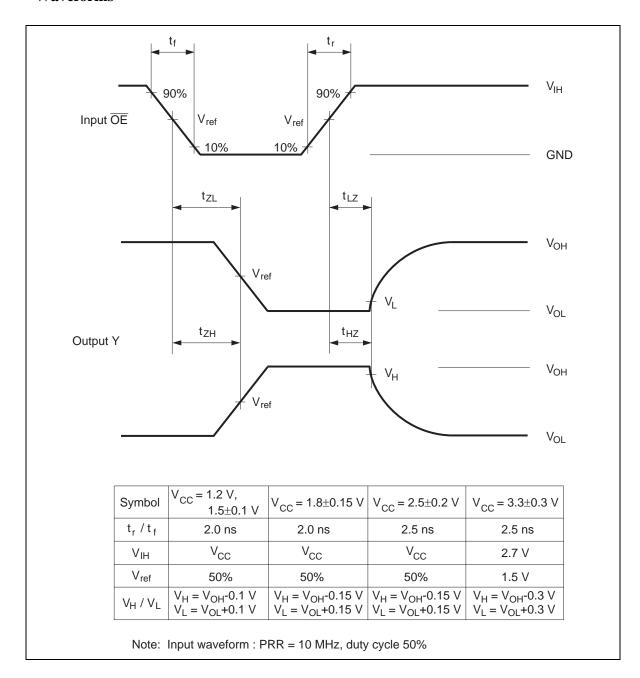
Waveforms



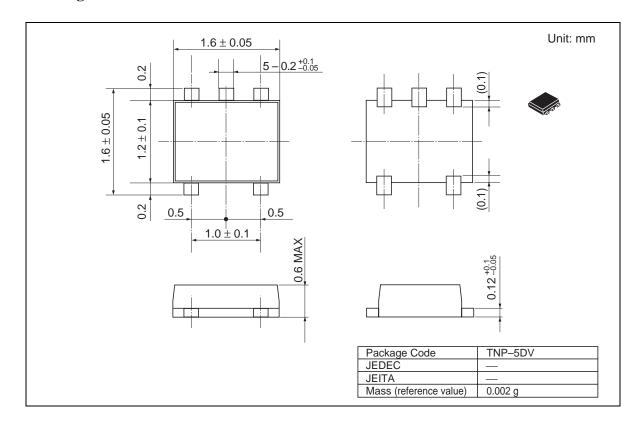
Test Circuit



Waveforms



Package Dimensions



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